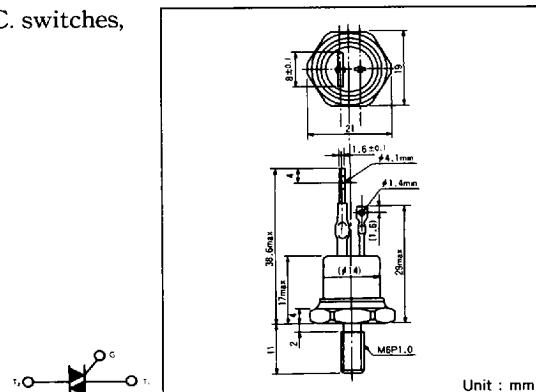


TRIAC SSG35C

For general A.C. power control applications such as A.C. switches, light controls, speed controls and heater controls etc.

- General A.C. power use
- $I_{T(RMS)} = 35A$
- High voltage up to 1200V
- High surge current of 400A
- Package types; stud



■ Maximum Ratings

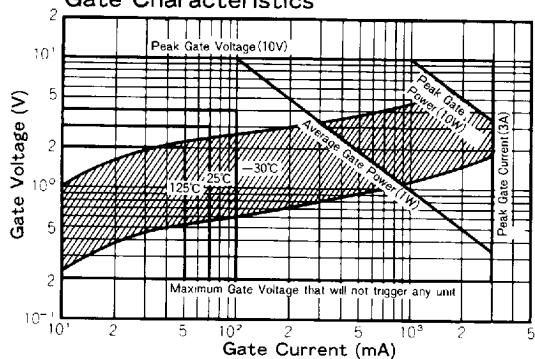
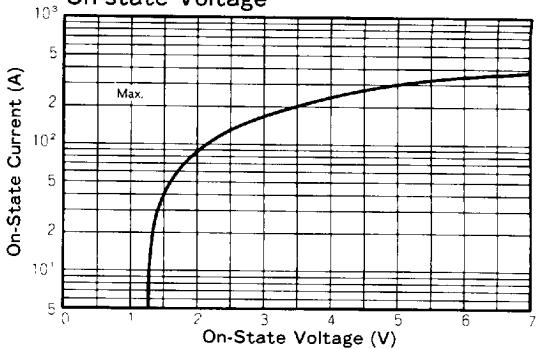
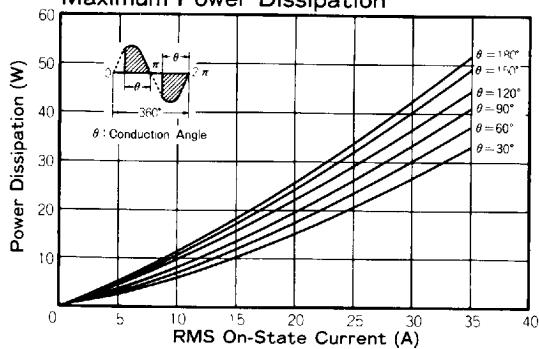
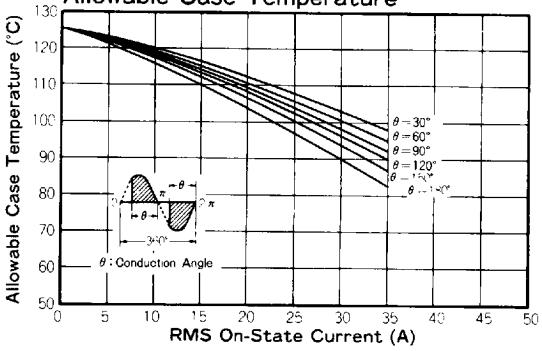
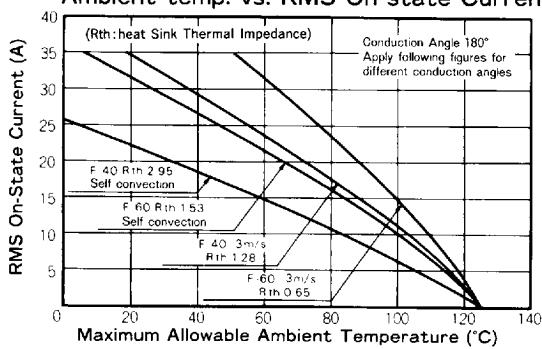
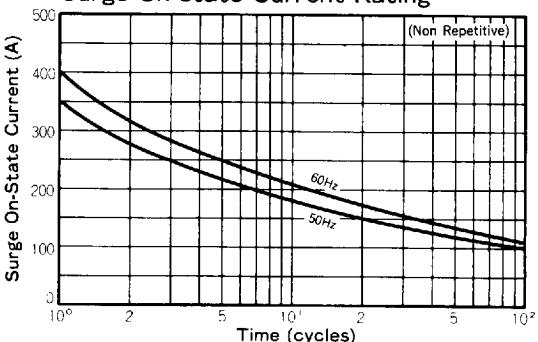
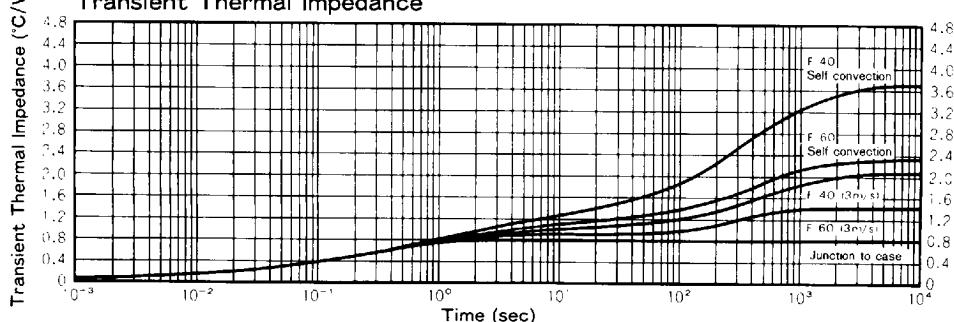
Symbol	Item	SSG35C40	SSG35C60	SSG35C80	SSG35C100	SSG35C120	Unit
V_{DRM}	Repetitive Peak Off-State Voltage	400	600	800	1000	1200	V
$I_{T(RMS)}$	R.M.S On-State Current					35	A
I_{TSM}	Surge On-State Current					350/400	A
I^2t	I^2t					660	A^2s
P_{GM}	Peak Gate Power Dissipation					10	W
$P_{G(AV)}$	Average Gate Power Dissipation					1	W
I_{GM}	Peak Gate Current					3	A
V_{GM}	Peak Gate Voltage					10	V
di/dt	Critical Rate of Rise of On-State Current	$I_0 = 100mA$, $T_j = 25^\circ C$, $V_D = \frac{1}{2} V_{DRM}$, $dI_G/dt = 1A/\mu s$				50	$A/\mu s$
T_j	Operating Junction Temperature					-30~+125	°C
T_{stg}	Storage Temperature					-30~+125	°C
	Mounting Torque	Recommended Value 20kgf·cm				25	kgf·cm
	Mass	Excluding nut & washer. 2.6g, and wrapping material 4g				22.5	g

■ Electrical Characteristics

Symbol	Item	Conditions	Ratings	Unit
I_{DRM}	Repetitive Peak Off-State Current, max.	at V_{DRM} , single phase, half wave, $T_j = 125^\circ C$	6	mA
V_{TM}	Peak On-State Voltage, max.	$I_T = 50A$ $T_j = 25^\circ C$ Inst. measurement	1.6	V
I_{GT1}^+	Gate Trigger Current, max.	$T_j = 25^\circ C$, $I_T = 1A$, $V_D = 6V$	70	mA
I_{GT1}^-		$T_j = 25^\circ C$, $I_T = 1A$, $V_D = 6V$	70	
I_{GT3}^+			—	
I_{GT3}^-		$T_j = 25^\circ C$, $I_T = 1A$, $V_D = 6V$	70	
V_{GT1}^+	Gate Trigger Voltage, max.	$T_j = 25^\circ C$, $I_T = 1A$, $V_D = 6V$	3	V
V_{GT1}^-		$T_j = 25^\circ C$, $I_T = 1A$, $V_D = 6V$	3	
V_{GT3}^+			—	
V_{GT3}^-		$T_j = 25^\circ C$, $I_T = 1A$, $V_D = 6V$	3	
V_{GD}	Non-Trigger Gate Voltage, min.	$T_j = 125^\circ C$, $V_D = \frac{1}{2} V_{DRM}$	0.2	V
t_{gt}	Turn On Time, max	$I_T = 35A$, $I_0 = 100mA$, $V_D = \frac{1}{2} V_{DRM}$, $T_j = 25^\circ C$ $dI_G/dt = 1A/\mu s$	10	μs
dv/dt	Critical Rate of Rise of On-State Voltage, min.	$T_j = 125^\circ C$, $V_D = \frac{2}{3} V_{DRM}$, Exponential wave.	100	$V/\mu s$
$(dv/dt)_c$	Critical Rate of Rise off-State Voltage at commutation, min	$T_j = 125^\circ C$, $(dv/dt)_c = 15A/ms$, $V_D = \frac{2}{3} V_{DRM}$	20	$V/\mu s$
I_H	Holding Current, typ.	$T_j = 25^\circ C$	30	mA
$R_{th(j-c)}$	Thermal Impedance, max.	Junction to case	0.8	$^\circ C/W$

■ 7991243 0002435 610 ■

SanRex

Gate Characteristics**On-state Voltage****On state Current vs. Maximum Power Dissipation****On state Current vs. Allowable Case Temperature****Ambient temp. vs. RMS On state Current****Surge On state Current Rating****Transient Thermal Impedance**

■ 7991243 0002436 557 ■

SANSHA ELECTRIC

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